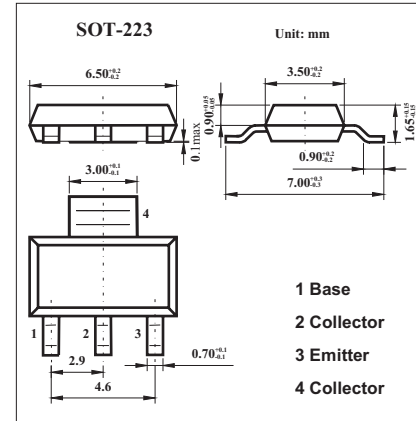


## PNP Silicon Planar High Voltage Transistor

## FZTA92

## ■ Features

- High breakdown voltage



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-300	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Base Current	I <sub>B</sub>	-100	mA
Continuous Collector Current	I <sub>C</sub>	-500	mA
Power Dissipation at Tamb=25°C	P <sub>tot</sub>	2	W
Operating and Storage Temperature Range	T <sub>J</sub> :T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-300			V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0*	-300			V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-200V, I <sub>E</sub> =0			-0.25	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V, I <sub>C</sub> =0			-0.1	μA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-20mA, I <sub>B</sub> =-2mA			-0.5	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-20mA, I <sub>B</sub> =-2mA			-0.9	V
Static Forward Current Transfer Ratio	h <sub>FE</sub>	I <sub>C</sub> =-1mA, V <sub>CE</sub> =-10V*	25			
		I <sub>C</sub> =-10mA, V <sub>CE</sub> =-10V*	40			
		I <sub>C</sub> =-30mA, V <sub>CE</sub> =-10V*	25			
Transition Frequency	f <sub>T</sub>	I <sub>C</sub> =-10mA, V <sub>CE</sub> =-20V, f=20MHz	50			MHz
Output Capacitance	C <sub>obo</sub>	V <sub>CB</sub> =-20V, f=1MHz			6	pF

\* Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%